TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP281,TLP281-4

PROGRAMMABLE CONTROLLERS **AC/DC-INPUT MODULE** PC CARD MODEM(PCMCIA)

TLP281 and TLP281-4 is a very small and thin coupler, suitable for surface mount assembly in applications such as PCMCIA Fax modem, programmable controllers.

TLP281 and TLP281-4 consist of photo transistor, optically coupled to a gallium arsenide infrared emitting diode.

 Collector-Emitter Voltage : 80 V (MIN) **Current Transfer Ratio** : 50% (MIN) Rank GB : 100% (MIN) Isolation Voltage : 2500 Vrms (MIN)

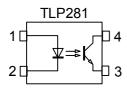
UL Recognized : UL1577, File No. E67349 **BSI** Approved : BS EN 60065: 1994,

> : BS EN 41003: 1997 Certificate No. 8143, 8144

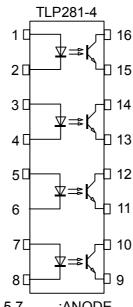
Unit in mm **TLP281** 7.0 ± 0.4 Half Pitch Mini Flat 4 pin **TOSHIBA**

Weight: 0.05 g

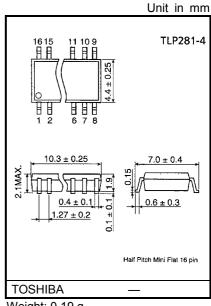
PIN CONFIGURATION(Top view)



1:ANODE 2:CATHODE 3:EMITTER 4:COLLECTOR



1,3,5,7 :ANODE :CATHODE 2,4,6,8 9,11,13,15 :EMITTER 10,12,14,16 :COLLECTOR



Weight: 0.19 g



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RAT	UNIT	
	CHARACTERISTIC	TLP281 TL		TLP281-4	UNIT
	Forward Current	<mark>l</mark> F	5	0	mA
	Forward Current Derating	ΔI _F /°C	−0.7 (Ta≥53°C)	-0.5 (Ta≥25°C)	mA /°C
ED	Pulse Forward Current	I _{FP}		Α	
	Reverse Voltage	V _R	Ę	5	V
	Junction Temperature	Tj	125		°C
	Collector-Emitter Voltage	V _{CEO}	8	V	
	Emitter-Collector Voltage	V _{ECO}	7	V	
S.	Collector Current	IC	50		mA
DETECTOR	Collector Power Dissipation (1 Circuit)	P _C	150	100	mW
ă	Collector Power Dissipation Derating(Ta≥25°C) (1 Circuit)	ΔP _C /°C	-1.5	-1.0	mW /°C
	Junction Temperature	Tj	125		°C
Оре	erating Temperature Range	T _{opr}	-55~100		°C
Sto	rage Temperature Range	T _{stg}	-55	°C	
Lead Soldering Temperature		T _{sol}	260 (10s)		°C
Total Package Power Dissipation (1 Circuit)		PT	200	170	mW
Total Package Power Dissipation Derating (Ta≥25°C) (1 Circuit)		ΔP _T /°C	-2.0	-1.7	mW /°C
Isol	ation Voltage (Note1)	BV _S	2500(AC,1mi	Vrms	

(Note1)Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_{F}	I _F = 10 mA	1.0	1.15	1.3	V
	Reverse Current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	_	pF
DETECTOR	Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C = 0.5 mA	80	_	_	V
	Emitter-Collector Breakdown Voltage	V _(BR) ECO	I _E = 0.1 mA	7	_	_	V
	Collector Dark Current	loro	V _{CE} = 48 V, Ambient Light Below (100 ℓx)	_	0.01 (2)	0.1 (10)	μA
	(Note2)	I _{CEO}	V _{CE} = 48 V, Ta = 85°C Ambient Light Below (100 ℓx)		2 (4)	50 (50)	μΑ
	Capacitance (Collector to Emitter)	C _{CE}	V = 0, f = 1 MHz	_	10	_	pF

(Note 2) Because of the construction,leak current might be increased by ambient light.

Please use photocoupler with less ambient light.

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I _C / I _F	I _F = 5 mA, V _{CE} = 5 V	50	_	600	- %
		Rank GB	100	_	600	
Saturated CTR	I _C / I _{F (sat)}	IF = 1 mA, VCE = 0.4 V		<mark>60</mark>	1	%
Cultifaced 6114		Rank GB	30	_	-	,0
Collector-Emitter		I _C = 2.4 mA, I _F = 8 mA	l	_	0.4	
Saturation Voltage	V _{CE (sat)}	I _C = 0.2 mA, I _F = 1 mA	1	0.2	_	V
Cataration voltage		Rank GB	_	_	0.4	
Off-State Collector Current	I _{C (off)}	V _F = 0.7 V, V _{CE} = 48 V		_	10	μA

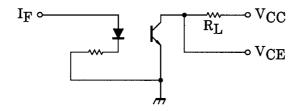
ISOLATION CHARACTERISTICS (Ta = 25°C)

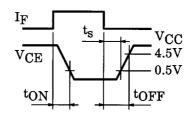
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C _S	V _S = 0 V, f = 1 MHz	_	0.8	_	pF
Isolation Resistance	R _S	V _S = 500 V, R.H.≤60%	5×10 ¹⁰	10 ¹⁴	_	Ω
	BV _S	AC , 1 minute	2500	_	_	Vrms
Isolation Voltage		AC , 1 second,in OIL	_	5000	_	
		DC , 1 minute, in OIL	_	5000	_	Vdc

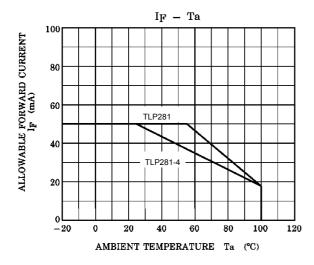
SWITCHING CHARACTERISTICS (Ta = 25°C)

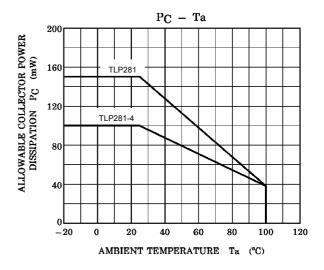
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t _r	$V_{CC} = 10 \text{ V}, I_{C} = 2 \text{ mA}$ $R_{L} = 100\Omega$	_	2	_	
Fall Time	t _f		_	3	_	ue
Turn-On Time	t _{on}		-	3	_	μs
Turn-Off Time	t _{off}		_	3	_	
Turn-On Time	toN	R_L = 1.9 kΩ (Fig.1) V_{CC} = 5 V, I_F = 16 mA	1	2	_	
Storage Time	ts		l	25		μs
Turn-Off Time	toff		_	40	_	

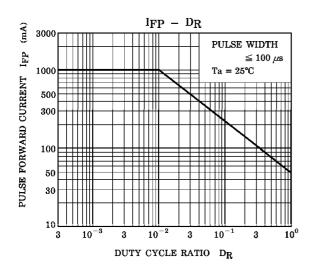
(Fig.1)SWITCHING TIME TEST CIRCUIT

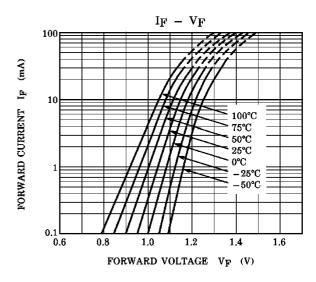


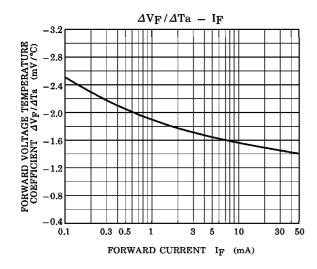


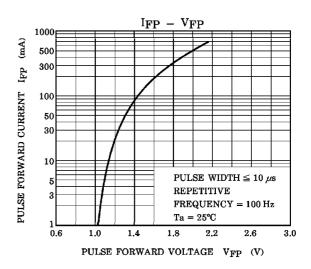




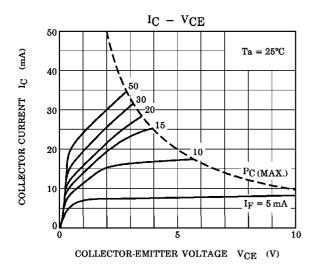


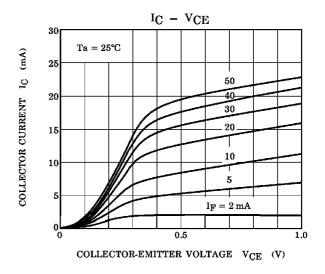


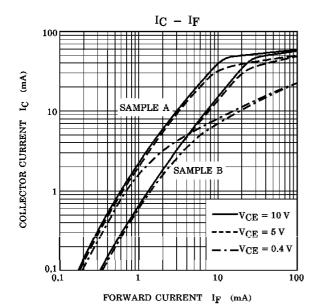


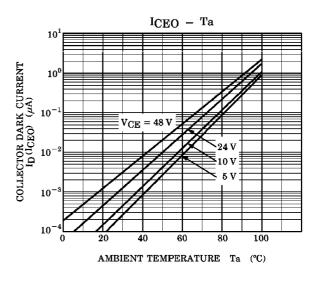


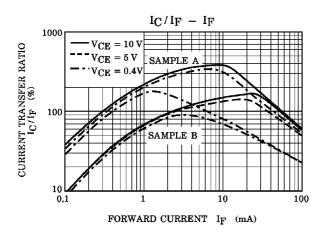
4



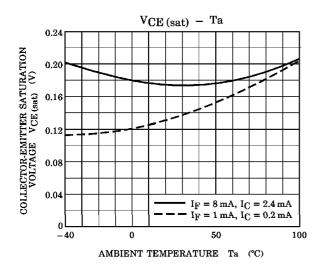


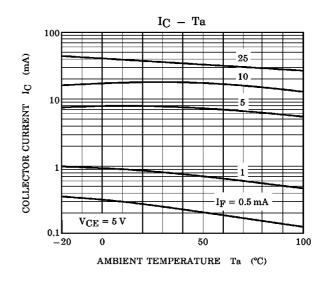


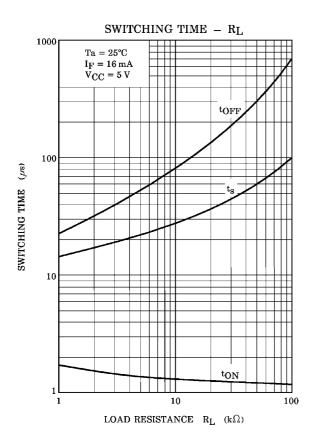


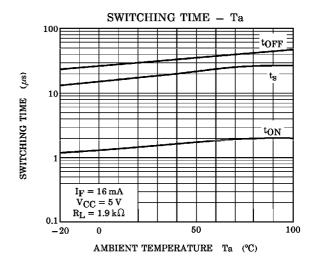


5 2002-06-27









RESTRICTIONS ON PRODUCT USE

000707EBC

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes
 are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the
 products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with
 domestic garbage.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other
 rights of the third parties which may result from its use. No license is granted by implication or otherwise under
 any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.